

**substance:** Co<sub>3</sub>O<sub>4</sub>

**property:** electrical conductivity, Seebeck coefficient

**conductivity:** Fig. 1. p-type semiconductor with room temperature resistivity of  $\approx 10^4 \Omega \text{ cm}$ .

**activation energy for conductivity**

$E_A$	0.4 eV	$T = 400 \dots 600 \text{ K}$	79G
	0.68 eV	$T = 450 \dots 500 \text{ K}$	38H

Co<sub>3</sub>O<sub>4.02</sub>

**Seebeck coefficient**

$S$	600 $\mu\text{V K}^{-1}$	$T = 300 \text{ K}$	78A
	1050 $\mu\text{V K}^{-1}$	$T = 300 \text{ K}$	79G

Co<sub>3</sub>O<sub>4</sub> can be synthesized grossly cation deficient [78B]. X-ray measurements indicate that the cation vacancies order to provide solid solutions between Co<sub>3</sub>O<sub>4</sub> and the hypothetical defect spinel  $\gamma\text{-Co}_2\text{O}_3$ . The formulation  $\text{Co}(\text{Co}_{2-x}^{3+}\text{Co}_{x/4}^{4+}\text{vac}_{3x/4})\text{O}_4$  has been suggested [78B] and conductivity and Seebeck data for films of non-stoichiometric oxide are shown in Fig. 2.

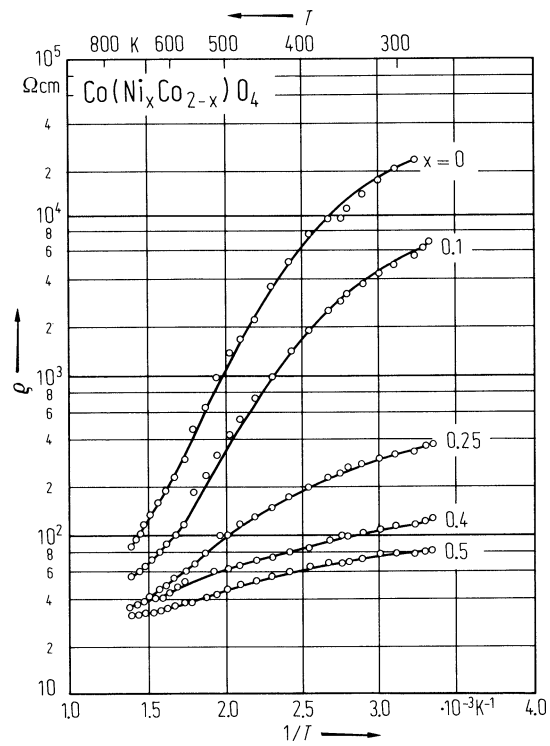
On doping with Zn the material remains p-type and semiconducting (Fig. 3). Doping with Ni leads to a semiconductor-semimetal transition at  $x \approx 0.5$  (Fig. 4). Doping with Li has a marked effect on conductivity, a increasing from  $\approx 10^{-5} \Omega^{-1} \text{ cm}^{-1}$  to  $\approx 1 \Omega^{-1} \text{ cm}^{-1}$  at 1 at% Li and RT [77V].

## References:

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**Fig. 1.**

$\text{Co}_3\text{O}_4$ ,  $\text{Co}(\text{Ni}_x\text{Co}_{2-x})\text{O}_4$  ceramic. Resistivity vs. reciprocal temperature for various  $x$  [78A].



**Fig. 2.**

$\text{Co}_{3-\delta}\text{O}_4$  film. I and II: conductivity vs. reciprocal temperature for films annealed at 350°C and 400°C, respectively. III: Seebeck coefficient vs. reciprocal temperature for a  $\text{Co}_3\text{O}_4$  film annealed at 400°C [78B].

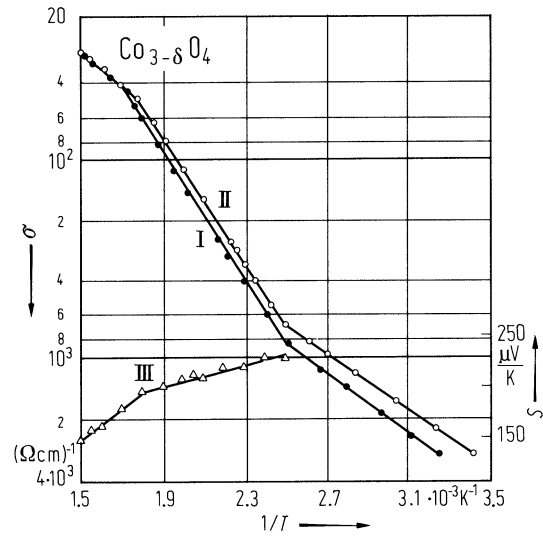


Fig. 3.

$(\text{Zn}_x\text{Co}_{1-x})\text{Co}_2\text{O}_4$  ceramic. Room temperature resistivity vs. composition [77V].

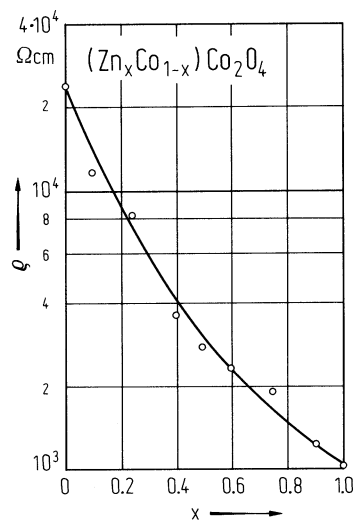


Fig. 4.

$\text{Co}(\text{Ni}_x\text{Co}_{1-x})\text{O}_4$  ceramic. Room temperature resistivity vs. composition [77V].

